

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE3401BY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -4.4A$

 $R_{DS(ON)} < 70 m\Omega$ @ V_{GS} =-2.5V

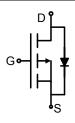
 $R_{DS(ON)}$ < 55m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 45m Ω @ V_{GS} =-10V

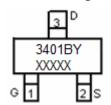
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

Package Marking And Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|------------|
| 3401BY | NCE3401BY | SOT-23-3L | Ø180mm | 8 mm | 3000 units |

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|----------------------|
| Drain-Source Voltage | V _{DS} | -30 | V |
| Gate-Source Voltage | V _{GS} | ±12 | V |
| Drain Current-Continuous | I _D | -4.4 | Α |
| Drain Current-Continuous(T _C =100°C) | I _D (100℃) | -3.1 | Α |
| Drain Current-Pulsed (Note 1) | I _{DM} | -30 | Α |
| Maximum Power Dissipation | P _D | 1.3 | W |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 150 | $^{\circ}\mathbb{C}$ |

Thermal Characteristic

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit | |
|---------------------------------|-------------------|--|------|------|------|------|--|
| Off Characteristics | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =-250μA | -30 | | - | V | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-24V,V _{GS} =0V | - | - | -1 | μA | |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±12V,V _{DS} =0V | - | - | ±100 | nA | |
| On Characteristics (Note 3) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=-250\mu A$ | -0.6 | -0.9 | -1.2 | V | |



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NCE3401BY

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|---|-----|-------|------|------|
| | | V _{GS} =-10V, I _D =-4A | - | 33 | 45 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =-4.5V, I _D =-3A | - | 37.5 | 55 | mΩ |
| | | V _{GS} =-2.5V, I _D =-2A | | 55 | 70 | mΩ |
| Forward Transconductance | g FS | V _{DS} =-5V,I _D =-4A | - | 10 | - | S |
| Dynamic Characteristics (Note4) | | • | | | | |
| Input Capacitance | C _{lss} | \/ - 15\/\/ -0\/ | - | 909.5 | - | PF |
| Output Capacitance | C _{oss} | V_{DS} =-15V, V_{GS} =0V, F=1.0MHz | - | 90.3 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0WHZ | _ | 71 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 7 | - | nS |
| Turn-on Rise Time | t _r | V _{DD} =-15V,I _D =-4A | - | 3.5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =-10 V , R_{GEN} =6 Ω | _ | 35 | - | nS |
| Turn-Off Fall Time | t _f | | - | 10 | - | nS |
| Total Gate Charge | Qg | | - | 7.3 | - | nC |
| Gate-Source Charge | Q _{gs} | V_{DS} =-15V, I_{D} =-4A, V_{GS} =-4.5V | _ | 1.1 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 2 | - | nC |
| Drain-Source Diode Characteristics | • | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =-4A | - | - | -1.2 | V |

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

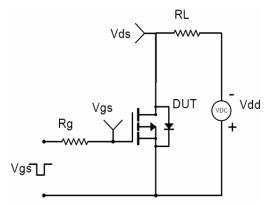


Figure 1:Switching Test Circuit

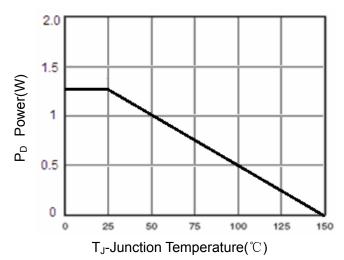


Figure 3 Power Dissipation

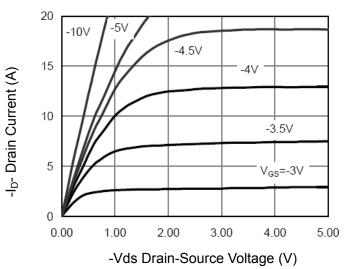


Figure 5 Output Characteristics

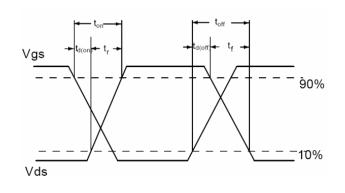


Figure 2:Switching Waveforms

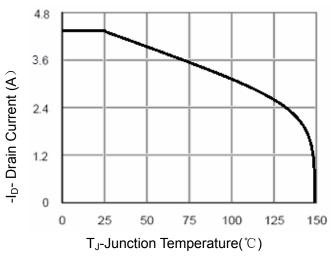
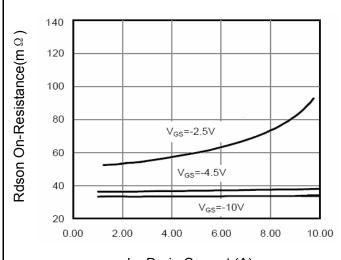


Figure 4 Drain Current



-I_D- Drain Current (A)

Figure 6 Drain-Source On-Resistance



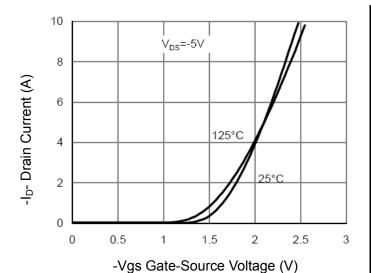
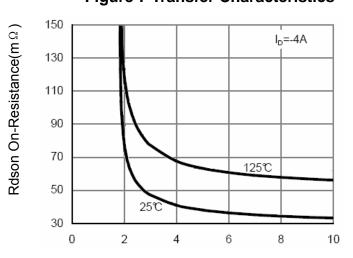


Figure 7 Transfer Characteristics



-Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

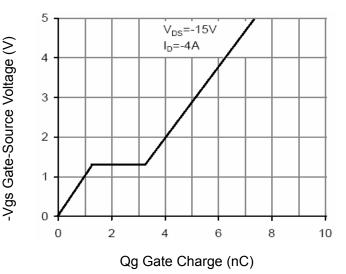
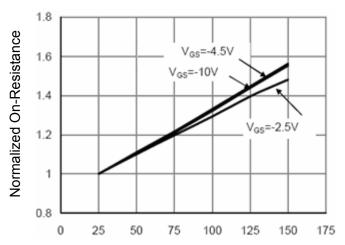
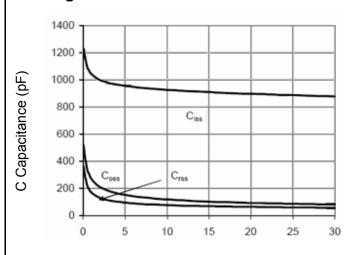


Figure 11 Gate Charge



 T_J -Junction Temperature(${}^{\circ}$ C) Figure 8 Drain-Source On-Resistance



-Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

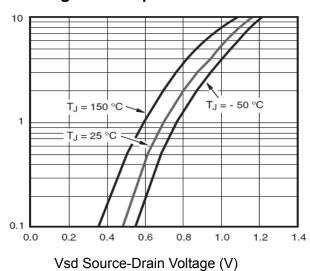
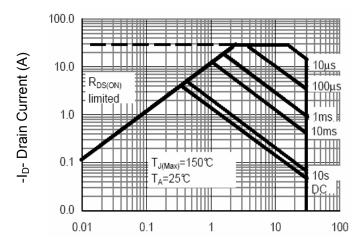


Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)





-Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

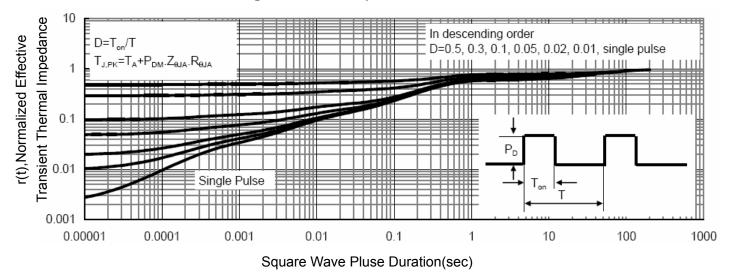
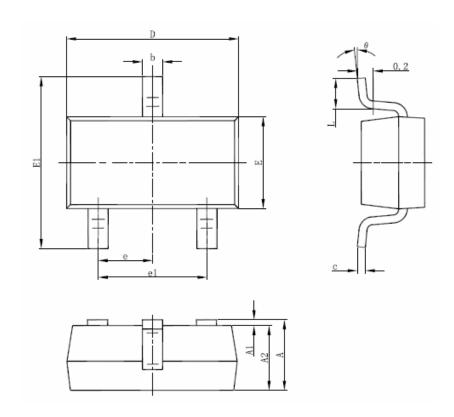


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



| Symbol | Dimensions In | Millimeters | Dimensions In Inches | | |
|--------|---------------|-------------|----------------------|-------|--|
| | Min | Max | Min | Max | |
| Α | 1.050 | 1.250 | 0.041 | 0.049 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.100 | 0.200 | 0.004 | 0.008 | |
| D | 2.820 | 3.020 | 0.111 | 0.119 | |
| E | 1.500 | 1.700 | 0.059 | 0.067 | |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 | |
| e | 0.950(BSC) | | 0.037(| BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.300 | 0.600 | 0.012 | 0.024 | |
| θ | 0° | 8° | 0° | 8° | |

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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